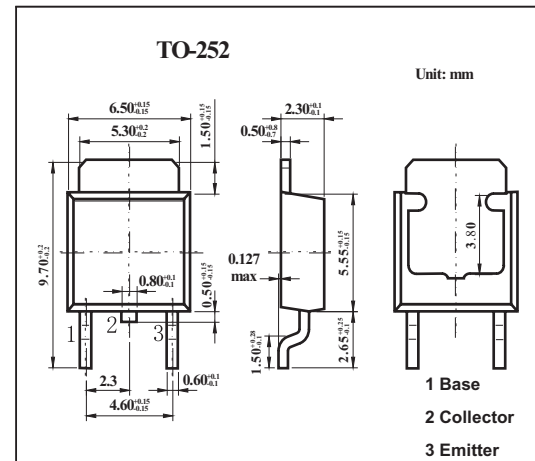


## High-Current Switching Applications

## 2SC4306

## ■ Features

- Low saturation voltage.
- Fast switching speed.
- Large current capacity.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

| Parameter                                       | Symbol    | Rating      | Unit             |
|---|-----------|-------------|------------------|
| Collector-base voltage                          | $V_{CB0}$ | 30          | V                |
| Collector-emitter voltage                       | $V_{CE0}$ | 20          | V                |
| Emitter-base voltage                            | $V_{EB0}$ | 5           | V                |
| Collector current                               | $I_C$     | 8           | A                |
| Collector current (pulse)                       | $I_{CP}$  | 12          | A                |
| Base current                                    | $I_B$     | 1.5         | A                |
| Collector dissipation<br>$T_c=25^\circ\text{C}$ | $P_C$     | 1           | W                |
|   | $P_C$     | 15          | W                |
| Junction temperature                            | $T_J$     | 150         | $^\circ\text{C}$ |
| Storage temperature                             | $T_{stg}$ | -55 to +150 | $^\circ\text{C}$ |

## 2SC4306

## ■ Electrical Characteristics Ta = 25°C

| Parameter                            | Symbol               | Testconditons                                | Min | Typ | Max | Unit |    |
|--------------------------------------|----------------------|--|-----|-----|-----|------|----|
| Collector cutoff current             | I <sub>CBO</sub>     | V <sub>CB</sub> = 20V, I <sub>E</sub> =0     |     |     | 1   | μA   |    |
| Emitter cutoff current               | I <sub>EBO</sub>     | V <sub>EB</sub> = 4V, I <sub>C</sub> =0      |     |     | 1   | μA   |    |
| DC current gain                      | h <sub>FE</sub>      | V <sub>CE</sub> = 2V, I <sub>C</sub> = 500mA | 100 |     | 400 |      |    |
|                                      |                      | V <sub>CE</sub> = 2V, I <sub>C</sub> = 6A    | 70  |     |     |      |    |
| Gain bandwidth product               | f <sub>T</sub>       | V <sub>CE</sub> = 2V, I <sub>C</sub> = 500mA |     | 250 |     | MHz  |    |
| Output capacitance                   | C <sub>ob</sub>      | V <sub>CB</sub> = 10V, f = 1.0MHz            |     | 60  |     | pF   |    |
| Collector-emitter saturation voltage | V <sub>CE(sat)</sub> | I <sub>C</sub> = 5A, I <sub>B</sub> = 250mA  |     | 220 | 400 | mV   |    |
| Base-emitter saturation voltage      | V <sub>BE(sat)</sub> | I <sub>C</sub> = 5A, I <sub>B</sub> = 250mA  |     | 1   | 1.3 | V    |    |
| Collector-base breakdown voltage     | V <sub>(BR)CBO</sub> | I <sub>C</sub> = 10μA, I <sub>E</sub> = 0    | 30  |     |     | V    |    |
| Collector-emitter breakdown voltage  | V <sub>(BR)CEO</sub> | I <sub>C</sub> = 1mA, R <sub>BE</sub> = ∞    | 20  |     |     | V    |    |
| Emitter-base breakdown voltage       | V <sub>(BR)EBO</sub> | I <sub>E</sub> = 10μA, I <sub>C</sub> = 0    | 5   |     |     | V    |    |
| Turn-on time                         | t <sub>on</sub>      |  |     | 30  | 300 | ns   |    |
| Storage time                         | t <sub>stg</sub>     |  |     |     | 250 | 1000 | ns |
| Fall time                            | t <sub>f</sub>       |  |     |     | 15  | 150  | ns |

## ■ hFE Classification

| Rank | R       | S       | T       |
|------|---------|---------|---------|
| hFE  | 100~200 | 140~280 | 200~400 |